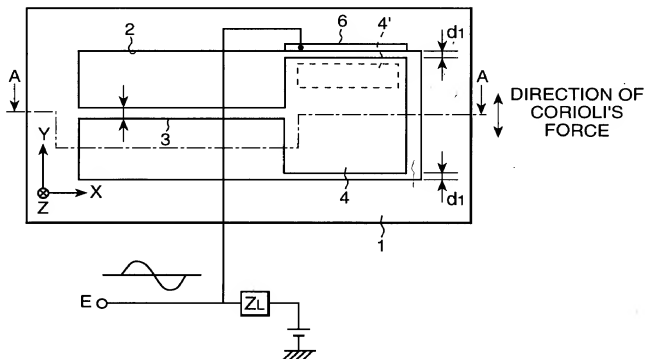
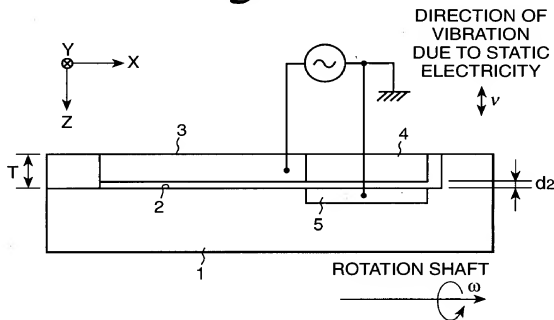


*Fig. 1*

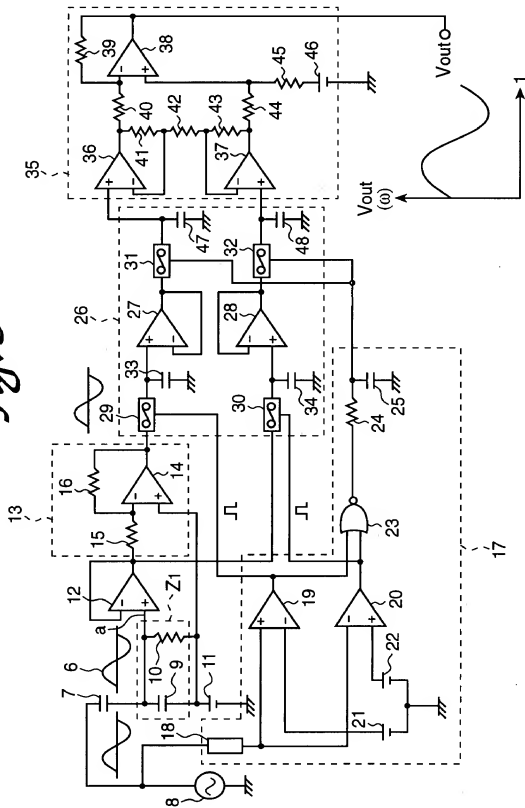


*Fig. 2*

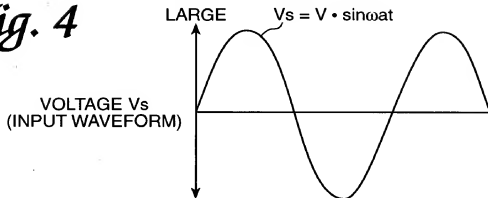


31 Figs.

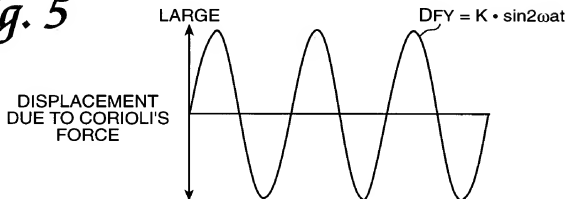
Fig. 3



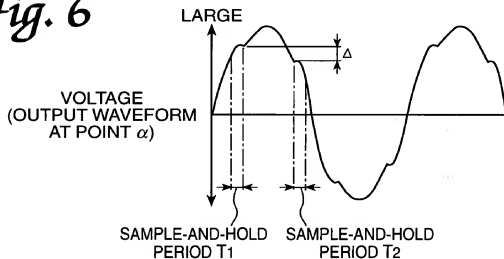
*Fig. 4*



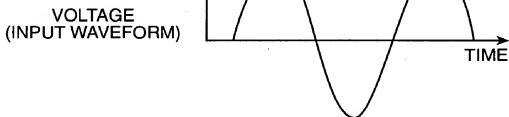
*Fig. 5*



*Fig. 6*



*Fig. 7*



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Fig. 8

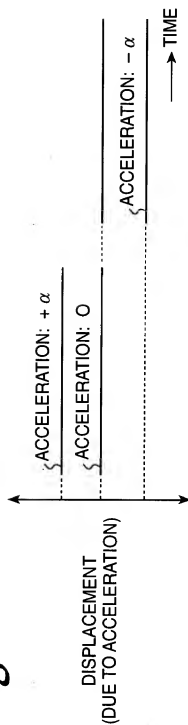
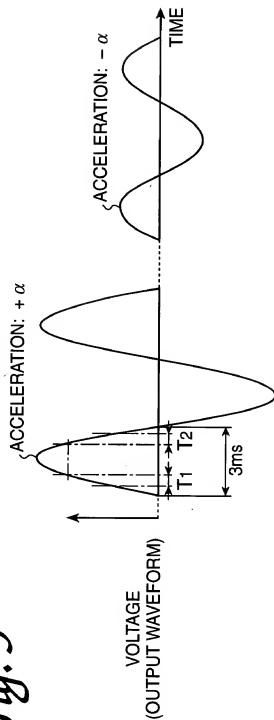
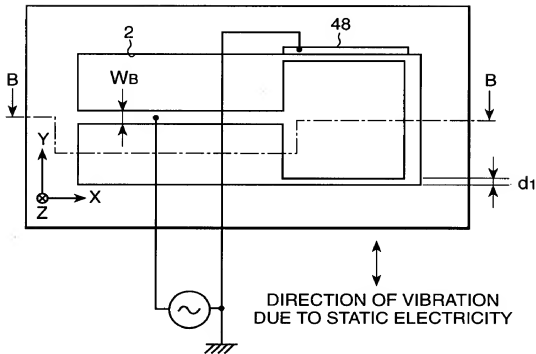


Fig. 9



*Fig. 10*



*Fig. 11*

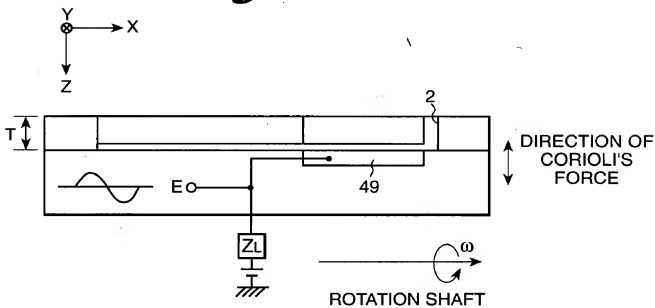
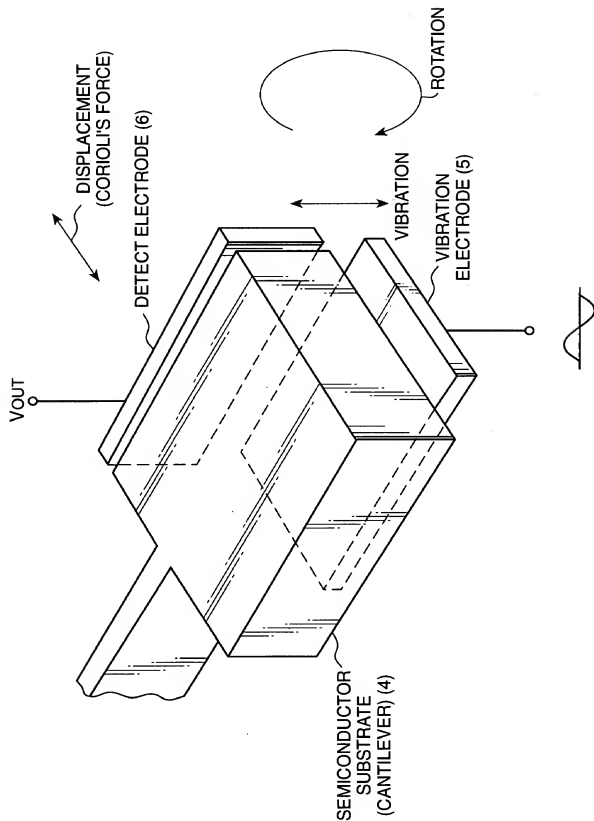


Fig. 12



00822T-66964260

Fig. 13

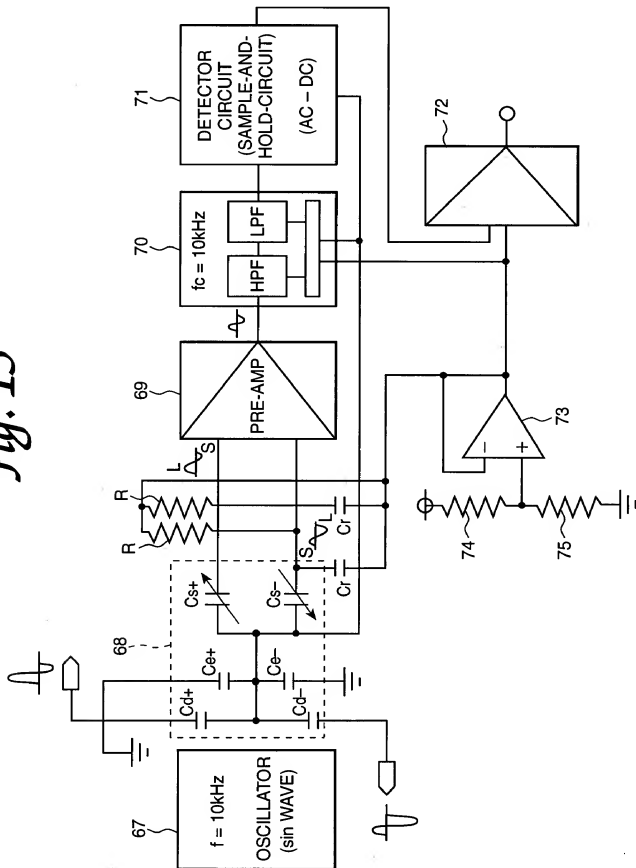
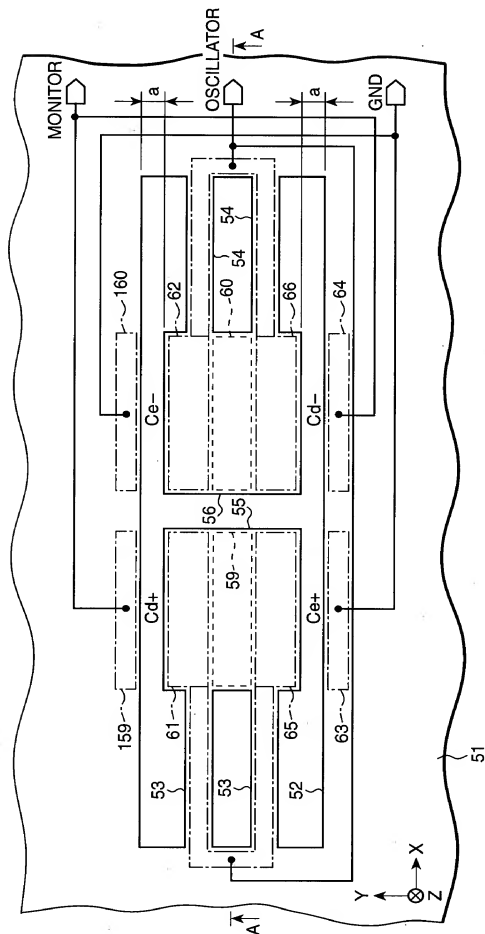


Fig. 14



008221-26964260



*Fig. 15*

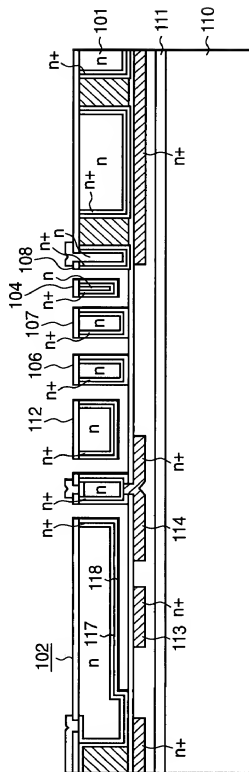
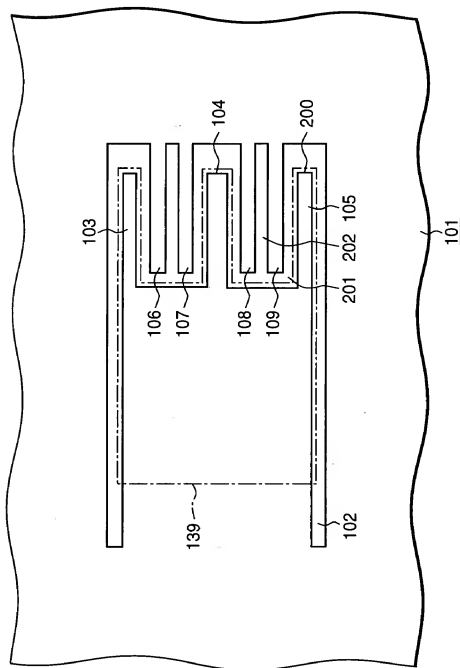


Fig. 17



008221-696460



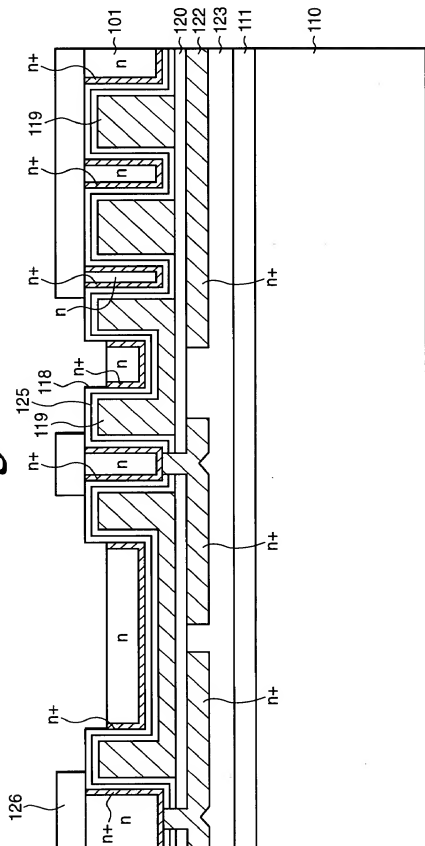
A cross-sectional view of a semiconductor device. The device consists of a substrate 101 with a top layer of material  $n$ . Below this layer, there is a series of rectangular structures. The top surfaces of these structures are labeled 117 and 118. The side surfaces are labeled  $n+$ . The bottom surfaces of the structures are labeled 116. The regions between the structures are labeled 115.

A diagram of a rectangular prism. The top face is labeled 111. The front face is labeled 110.

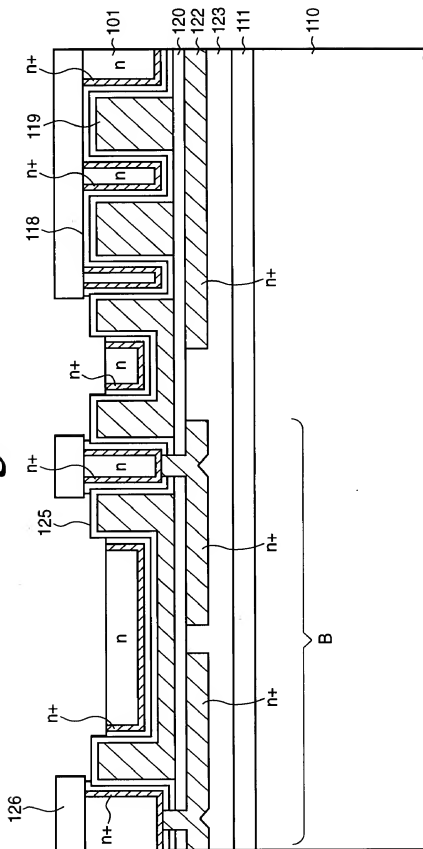
[illegible]

00822T-E6964Z60

Fig. 24

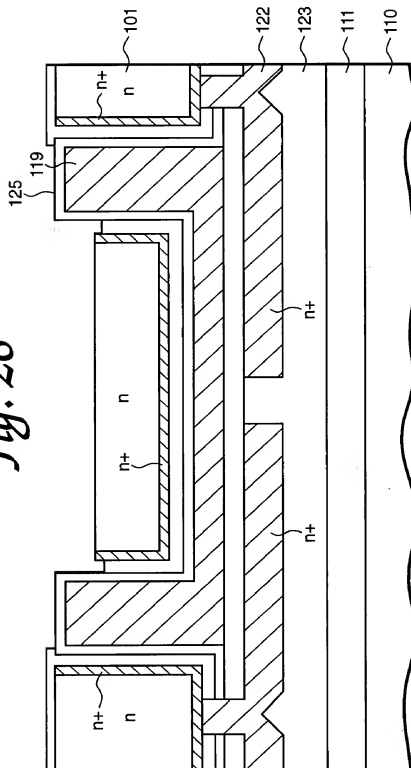


*Fig. 25*



008227-66964260

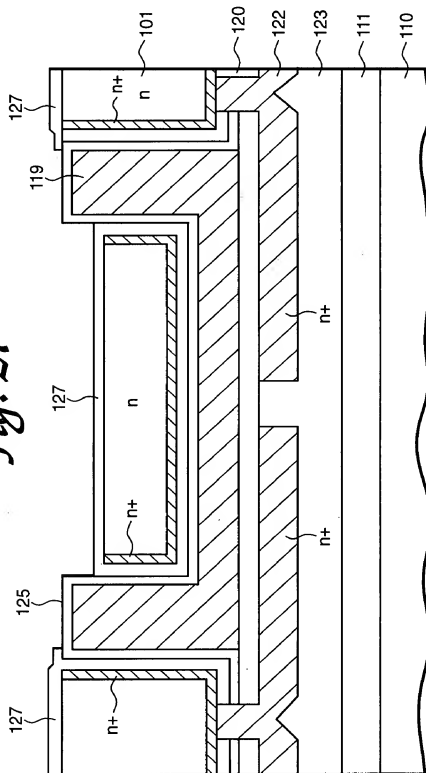
*Fig. 26*





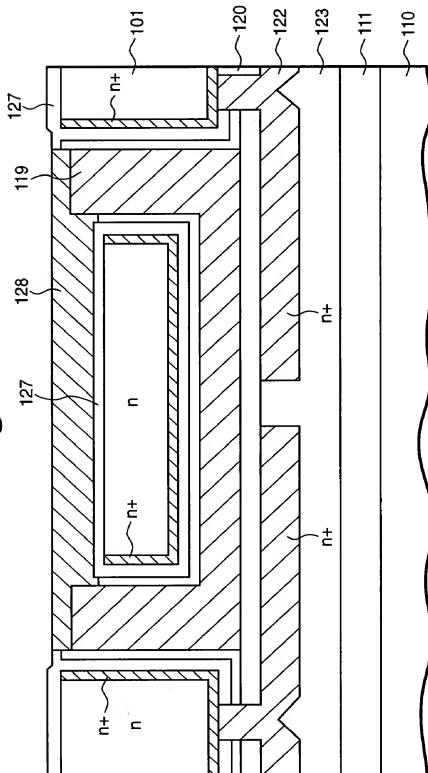
008221-EG964269

*Fig. 27*



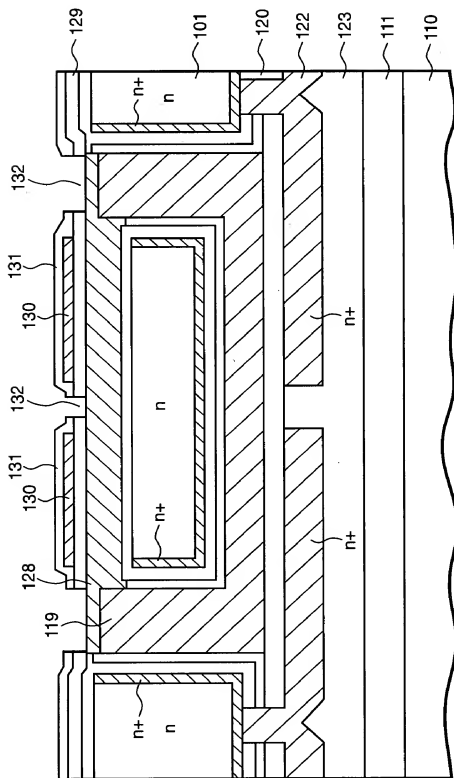
00822T" 86964/60

Fig. 28



008221-6696760

Fig. 29



003227-86964260

Fig. 30

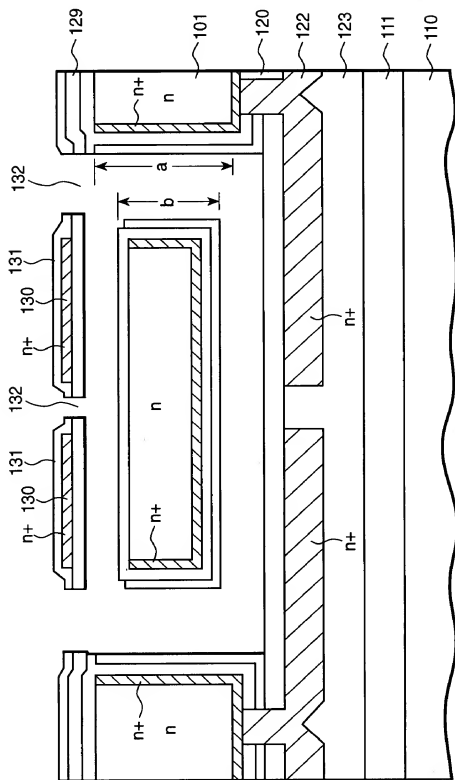
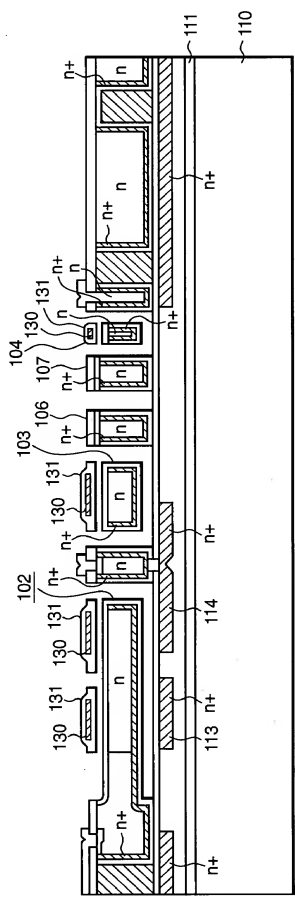


Fig. 31



00922T-26964260